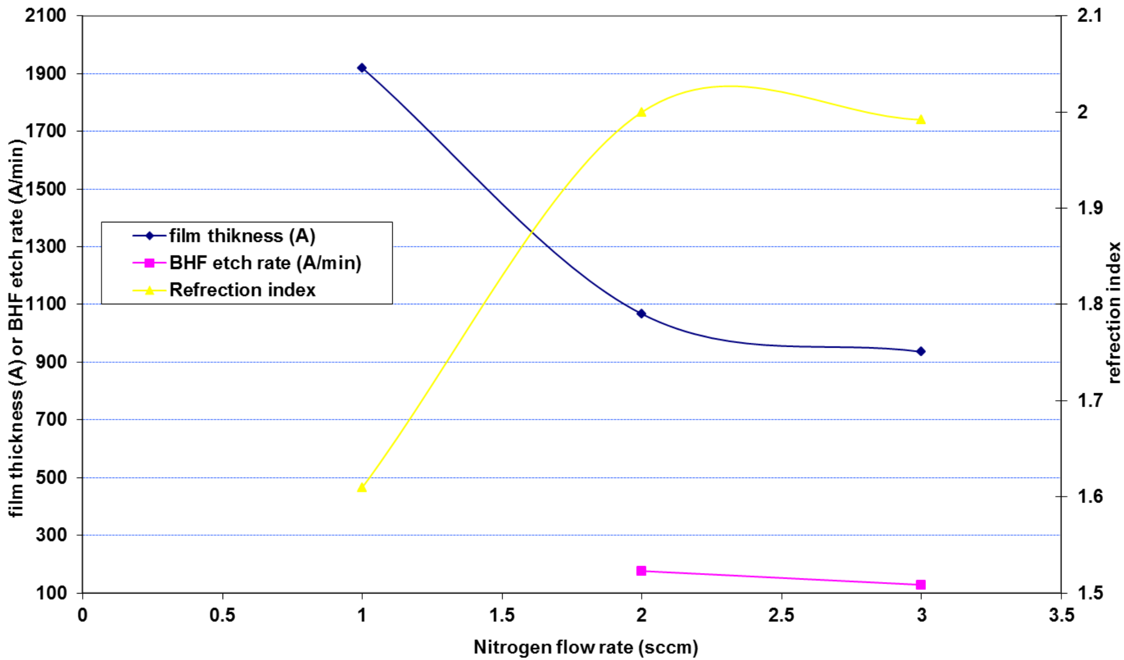
SiN Reactive Sputtering – N_2 Flow Data AJA1

Thickness - Index - Etch Rate – vs N2 flow: 1 hour: Ar 25sccm; 200W RF; Bias 10W; 3mT; Ht/Tilt 25/9



AFM – vs N2 flow: 1 hour: Ar 25sccm; 200W RF; 3mT; Ht/Tilt 25/9; Room T

AFM Measurements SiN AJA1

Ar-25sccm, 3mT, 200W, 1 hour, Ht/Tilt 25/9

Gas flow	Bias	name	roughness in nm		
			R_q	R_a	R_{max}
1 N_2	10 W	r	0.0454	0.0361	0.3600
2 N_2	10 W	s	0.0748	0.0593	1.1700
3 N_2	10 W	u	0.0769	0.0608	0.7050

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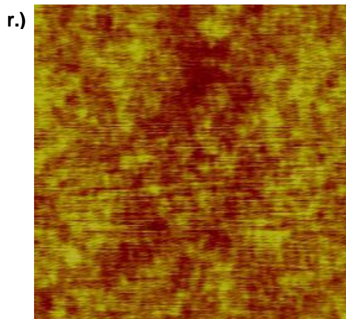

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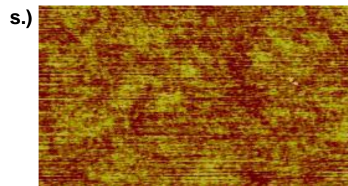

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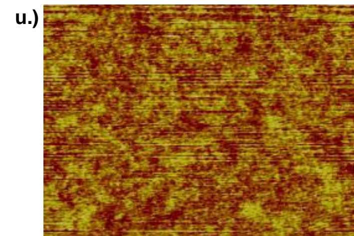

Thickness - Index - vs RF Power: 1 hour: N2/Ar 2.5/25sccm; Bias 10W; 3mT; Ht/Tilt 25/9